

SEMICONDUCTOR INTEGRATED CIRCUIT DEVICE HAVING BODY
BIASING CIRCUIT FOR GENERATING FORWARD WELL BIAS
VOLTAGE OF SUITABLE LEVEL BY USING SIMPLE CIRCUITRY

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ABSTRACT OF THE DISCLOSURE

10 A semiconductor integrated circuit device has a
MISFET and a body biasing circuit. The MISFET has a
source electrode and a drain electrode of a first
conductivity type and a gate electrode, and the MISFET is
formed in a well of a second conductivity type. The body
15 biasing circuit generates a voltage in the well by
passing a prescribed current in a forward direction into
a diode which is formed from the well and the source
electrode of the MISFET.